

## P-N Junction Diode

### Pure Semiconductor

- External atoms are not added.
- Ex: Si (Pure), Ge
- **INTRINSIC**

### Impure Semiconductor

- External atoms are added.
- Conductivity changes ( $\epsilon^0$ )
- **EXTRINSIC**

→ **Quality changes**

n-type

p-type

### N-type

- Pentavalent ( $5e^0$ s)
- Phosphorous



- Donor Impurity
- 

### p-type

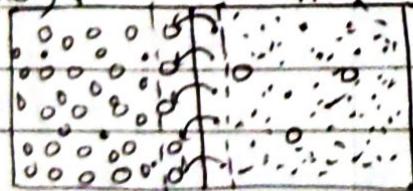
- Trivalent ( $3e^0$ s)
- Al → 13  
2, 8, 13

→ Acceptor Impurity

- Si needs 4  $e^0$ s for forming covalent bond.

- Pentavalent →  $5e^0$ s
- Trivalent →  $3e^0$ s

(maj. holes) p



$e^0$  moves (current)

n (maj.  $e^0$ s)

$\rightarrow e^0$ s  
0 → holes

Negative -ve

E.F

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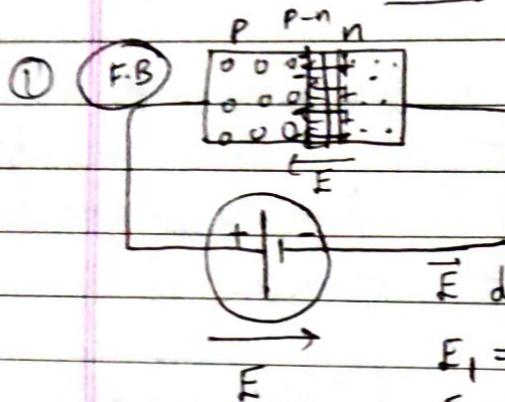
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## FORWARD AND REVERSE BIAS



$\vec{E}$  directions are opposite in nature

$$E_1 = 80$$

overall

$$E_2 = 60$$

$$E = 80 - 60 = 20 \text{ } E \downarrow$$

(less energy required)  
without sufficient

Potential barrier

$$V = E \cdot d$$

$$V_F$$

$$I_F$$

$$0$$

$$0$$

$$10$$

$$0$$

$$2$$

$$0$$

$$3$$

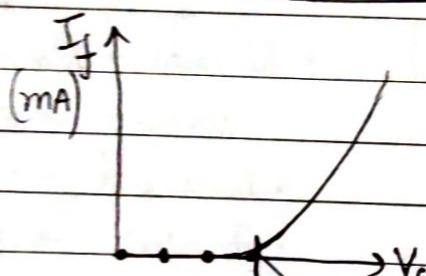
$$0$$

$$4$$

$$1$$

$$5$$

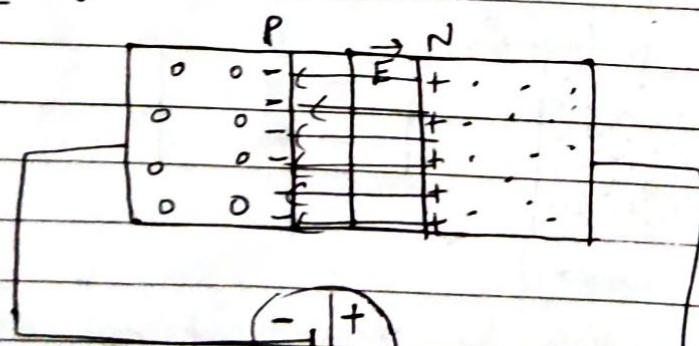
$$2$$



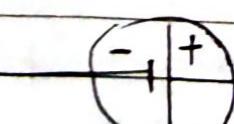
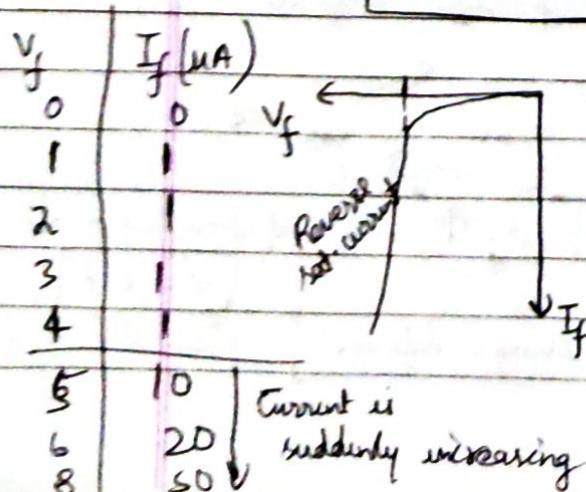
Cut off voltage or knee voltage

or Threshold voltage

### ② Reverse Biasing



→ Electric current is due to only minority charge carriers.



$$E_1, E_2 \quad (\vec{E} \text{ are in same direction})$$

$$E = E_1 + E_2$$

$$\uparrow E = 80 + 60$$

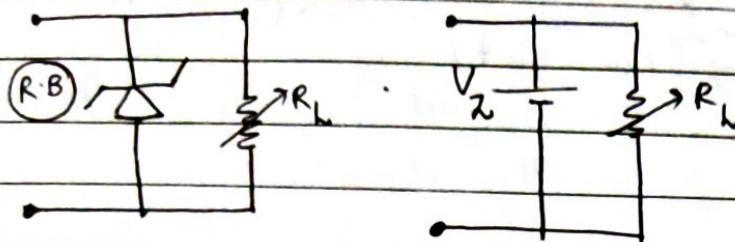
$$\uparrow E = V \uparrow$$

Pot. barrier

More energy required  
Less current found

## Zener Diode :-

→ Zener Diode is a special Diode → Acts as Voltage Regulator.



## Avalanche Breakdown :-

Lightly Doped Diodes [Normal Diode]

## Zener Breakdown :-

→ Highly Doped Diode → Breakdown is achieved much earlier  
 → "Rupture" → Jearing ↑ E·F

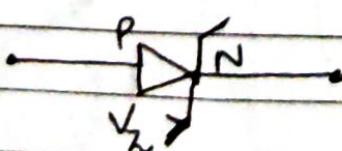
→ High Power Dissipation capability

Zener Diode > Normal Diode

→ Properties will not degrade.

<sup>for</sup> → Zener Diode in F-B region is same as Normal Diode in F-B region

## Symbol :-



$V_Z \rightarrow$  Zener Voltage

$$\gamma_Z = \frac{1}{slope}$$

Reverse Biased Region

Open circuit

$$V_Z = V_{Z0} + I_Z \gamma_Z$$

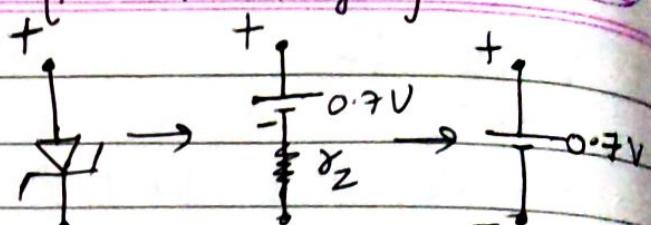
$$V_{Z0}, \gamma_Z$$

$I_{ZK}$  (knee current)

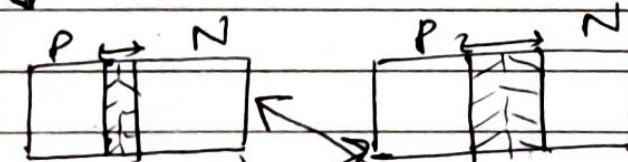
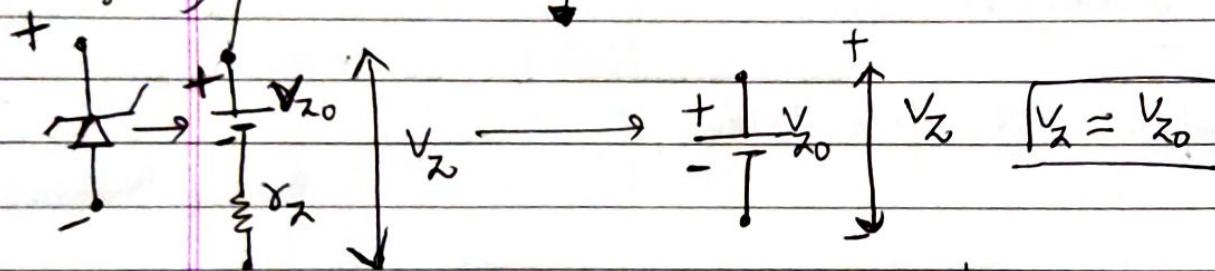
Forward Biased Region

Short circuit

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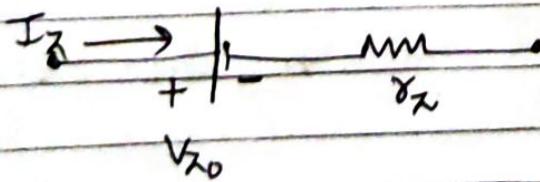
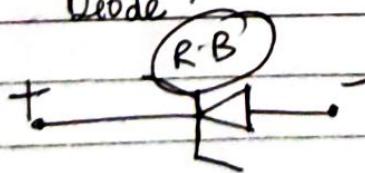
(Zener breakdown  
Region)



(Normal Diode)  
Dep Layer

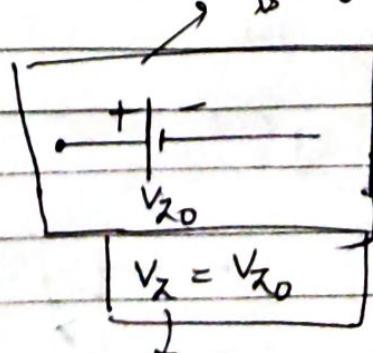
(Zener Diode Depletion Layer)

→ Depletion layer in case of Zener Diode is very thin as compared to depletion layer in case of Normal Diode.



$$V_Z = V_{Z0} + I_Z \gamma_Z$$

here  $R_Z$   
is neglected



$$V_Z = V_{Z0}$$

Used in Numericals

## Temperature Effect on Zener Voltage :-

$$\text{Temp. coefficient } T_c = \frac{\Delta V_z / V_z}{T_1 - T_0} \times 100\% / {}^\circ\text{C}$$

$\Delta V_z \rightarrow$  change in Zener Voltage

$V_z \rightarrow$  Zener Potential (Voltage) at  $25^\circ\text{C}$ .

$T_1 \rightarrow$  New temp.

$T_0 \rightarrow$  Room Temp ( $25^\circ\text{C}$ )

Q. Calculate change in Zener Voltage if zener voltage is 10V at  $25^\circ\text{C}$ , and new temp. is  $100^\circ\text{C}$ . Temp-coefficient ( $T_c$ ) is  $0.072\% / {}^\circ\text{C}$ .

Ans  $\Delta V_z = ?$   $T_0 = 25^\circ\text{C}$

$$V_z = 10\text{ V}$$

$$T_1 = 100^\circ\text{C}$$

$$T_c = 0.072\% / {}^\circ\text{C}$$

$$T_c = \frac{\Delta V_z / V_z}{(T_1 - T_0)} \times 100\% / {}^\circ\text{C}$$

$$\Delta V_z = \frac{T_c V_z}{100\%} \cdot (T_1 - T_0)$$

$$\Rightarrow \frac{(0.072\% / {}^\circ\text{C}) (10) (100 - 25)}{100}$$

$$\Delta V_z \Rightarrow 0.54\text{ Volts}$$

$$\text{New zener potential} = V_z + \Delta V_z$$

$$= 10\text{ V} + 0.54\text{ V}$$

$$\Rightarrow 10.54\text{ V}$$

$$\uparrow T \quad V_z \uparrow$$

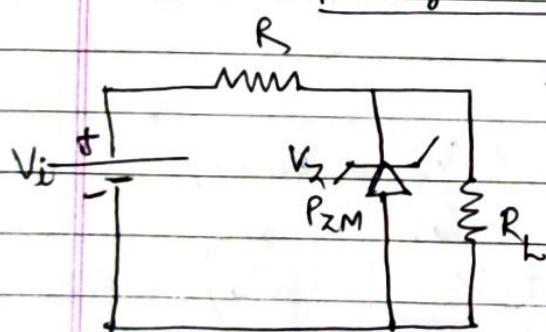
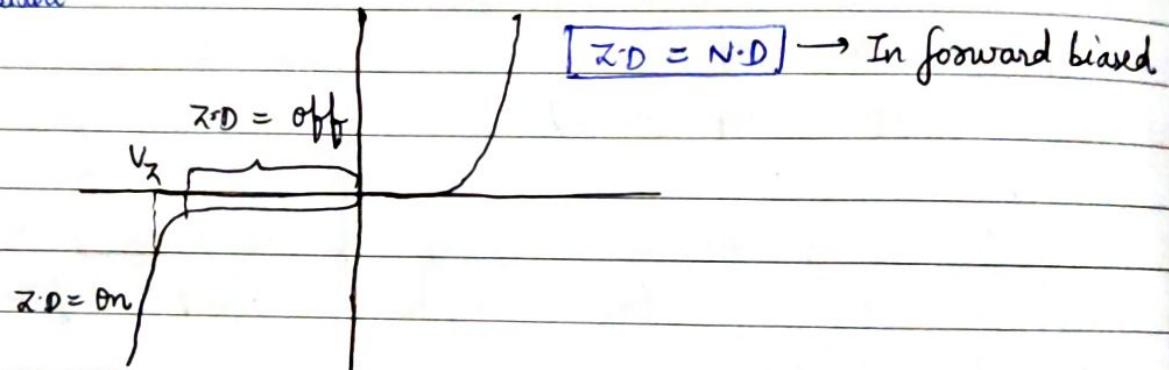
$$25^\circ\text{C} \rightarrow 10\text{ V}$$

$$100^\circ\text{C} \rightarrow 10.54\text{ V}$$

① Zener Diode as Voltage Regulator  $\rightarrow [V_i \text{ and } R_L \text{ fixed}]$

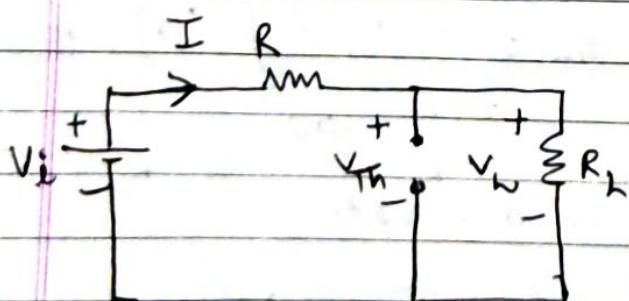
Q What is Voltage Regulator?

Ans: A voltage regulator is a combination of elements designed to ensure that the output voltage of a supply remains constant.



Case :-

- i)  $V_i$  and  $R_L$  fixed
- ii)  $V_i$  fixed and  $R_L$  is variable
- iii)  $V_i$  variable and  $R_L$  is fixed
- iv)  $V_i$  and  $R_L$  variable.



$$V_i - IR - IR_L = 0$$

$$I = \frac{V_i}{R + R_L}$$

$$\begin{aligned} V_{Th} &= V_L = IR_L \\ &= \frac{V_i R_L}{R + R_L} \end{aligned}$$

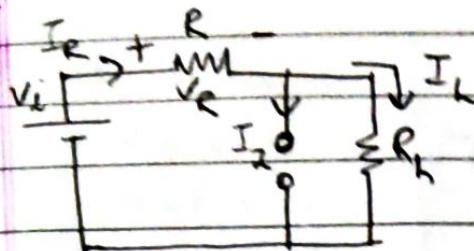
Case I:  $V_{Th} \geq V_Z \rightarrow$  On diode

Case II:  $V_{Th} < V_Z \rightarrow$  Diode is off

open circuit

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case①  $V_{Th} < V_Z$  [Zener  $\uparrow$  diode is off]



$$I_Z = 0$$

$$P_Z = I_Z \cdot V_Z = 0$$

$$I_R = I_L + I_Z^0$$

$$I_R = I_L$$

$$I_R = \frac{V_i}{R + R_L} = I_L$$

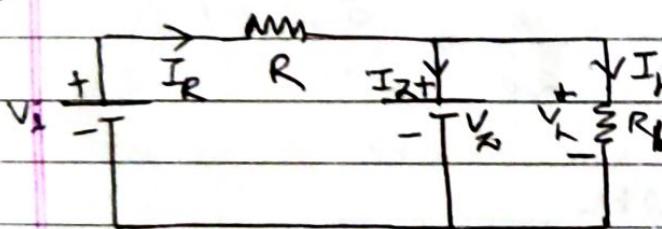
$$V_R = I_R R$$

$$V_L = I_L \cdot R_L$$

$$V_R = \frac{V_i \cdot R}{R + R_L}$$

$$V_L = \frac{V_i \cdot R_L}{R + R_L}$$

case②  $V_{Th} \geq V_Z$  [Zener Diode is on]



$$I_R = I_L + I_Z$$

$$I_Z = I_R - I_L$$

$$I_R = \frac{(V_i - V_Z)}{R}$$

$$I_L = \frac{V_L}{R_L}$$

$$V_Z = V_L$$

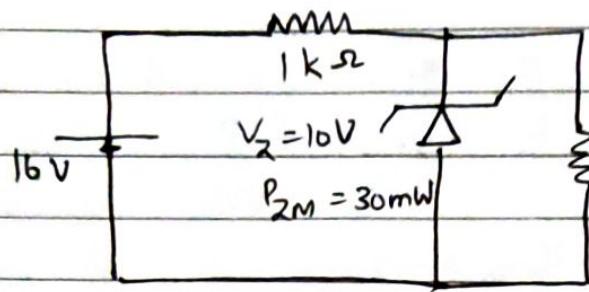
$$I_Z = \frac{V_Z}{R_L}$$

$$I_Z = \frac{(V_i - V_Z)}{R} - \frac{V_Z}{R_L}$$

$$P_Z = I_Z V_Z$$
$$= \left[ \frac{(V_i - V_Z)}{R} - \frac{V_Z}{R_L} \right] \times V_Z$$

$$P_Z < P_{ZM}$$

Q for the zener diode network, determine  $V_L$ ,  $V_R$ ,  $I_Z$ ,  $P_Z$



Given :-

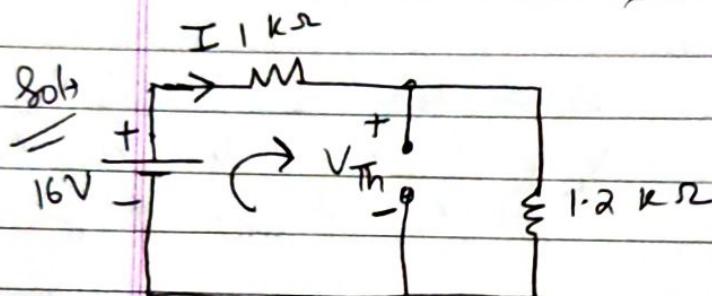
$$V_i = 16 \text{ V}$$

$$R = 1 \text{ k}\Omega$$

$$R_L = 1.2 \text{ k}\Omega$$

$$V_Z = 10 \text{ V}$$

$$P_{ZM} = 30 \text{ mW}$$



$$16 - I \times 1 - I \times 1.2 = 0$$

$$I = \frac{16}{1+1.2} = \frac{16}{2.2} = 7.27 \text{ mA}$$

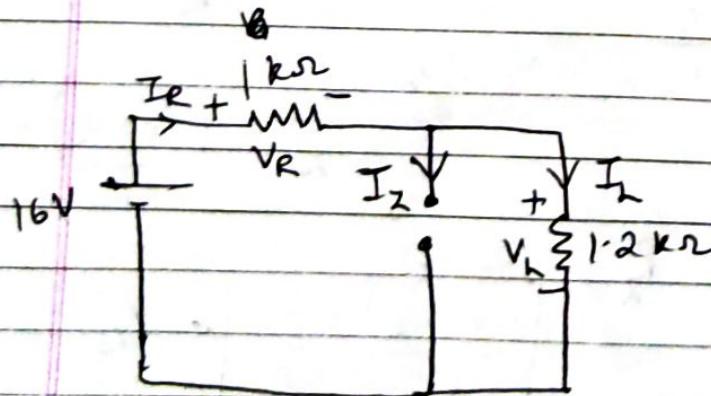
$$V_{Th} = V_L = I \times 1.2 \text{ k}\Omega$$

$$= 7.27 \times 1.2 \text{ k}\Omega$$

$$V_{Th} = 8.27 \text{ V}$$

$$V_{Th} < V_Z \rightarrow \text{So Zener}$$

Diode remains off.



$$I_R = I_L$$

$$I_Z = 0 \quad P_Z = 0$$

$$V_R = I_R \cdot (1 \text{ k}\Omega)$$

$$V_R = 7.27 \times 1 \text{ k}\Omega$$

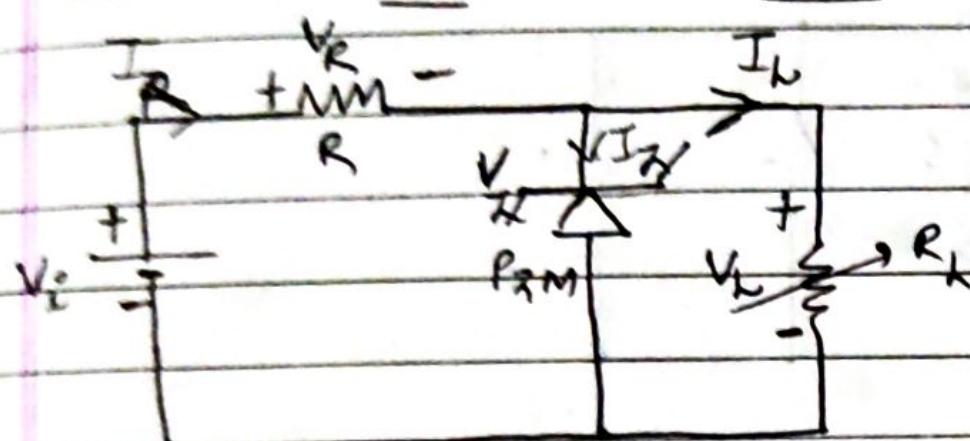
$$\boxed{V_R = 7.27 \text{ V}}$$

$$V_L = I_L \times 1.2 \text{ k}\Omega$$

$$V_L = 7.27 \times 1.2 \text{ k}\Omega$$

$$\boxed{V_L = 8.64 \text{ V}}$$

② Zener Diode as Voltage Regulator [  $V_i$  fixed &  $R_L$  variable ]



$$I_R = I_Z + I_L$$

$\downarrow \min \quad \downarrow \max$

$$I_{Z\min} = I_R - I_{L\max}$$

Cond' for minimum load resistance [ $R_L$ ] :-

Voltage across Z-D =  $V_Z$

$$V_L = V_R = V_{Th} = \frac{V_i \cdot R_L}{R + R_L} = V_Z$$

$$V_i - I_R \cdot R_L = 0$$

$$I = \frac{V_i}{R + R_L}$$

$$V_Z(R + R_L) = V_i R_L$$

$$R_{L\min} = \frac{V_Z R}{V_i - V_Z}$$

Cond' for max  $R_L$  :-

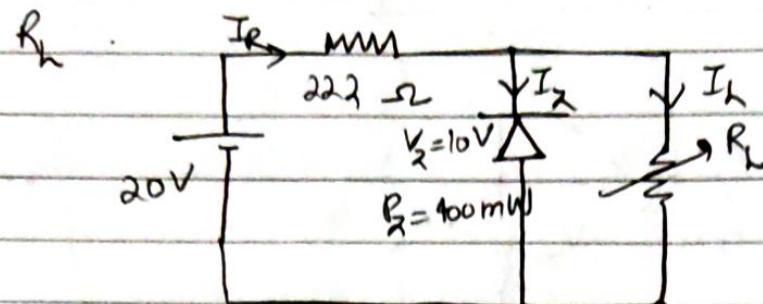
$$R_{L\max} = I_{L\min} = I_{Z\max}$$

$$P_{Zm} = I_{Z\max} \cdot V_Z$$

$$I_{L\max} = \frac{V_h}{R_{L\min}} = \frac{V_h}{R_{L\min}}$$

Q. Determine the minimum and maximum values of load resistance

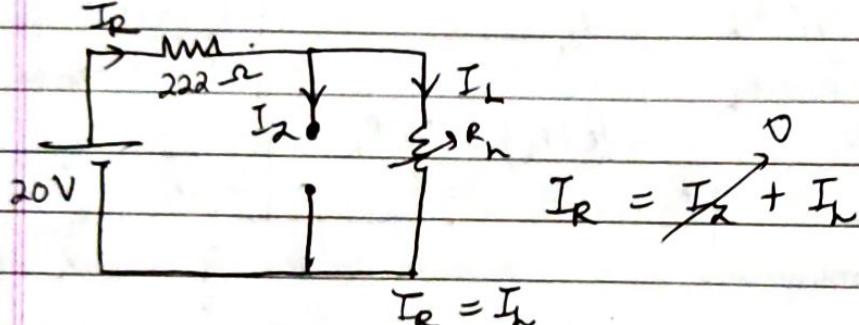
Q. Determine the minimum and maximum values of load resistance.



Sol: Case(I) for  $R_L$  to be min.:

$$R_{L\min} \rightarrow I_{L\max} \rightarrow I_{Z\min} \rightarrow 0 \quad (\text{open circuit})$$

when diode  
is off



$$20 - 222 I_R - I_L \cdot R_L = 0 \quad V_L = V_Z$$

$$20 - 222 I_R - I_R \cdot R_L = 0$$

$$20 = 222 I_R + I_R \cdot R_L$$

$$20 = I_R (222 + R_L)$$

$$I_L = I_R = \frac{20}{222 + R_L}$$

$$V_L = I_R \cdot R_L$$

$$10 = \frac{20}{222 + R_L} \cdot R_L$$

$$222 + R_L = 2 R_L$$

$$\boxed{\frac{1}{R_L} = \frac{2}{222}}$$

Case(II) for  $R_L$  to be max.:

$$R_{L\max} \rightarrow I_{L\min} \rightarrow I_{Z\max}$$

$$P_{Z\max} = I_{Z\max} V_Z$$

$$I_R = I_{L\min} + I_{Z\max}$$

$$I_R - I_{L\min} = I_{Z\max}$$

$$I_{Z\max} = \frac{P_{ZM}}{V_Z} = \frac{40\phi}{10}$$

$$R_{L\max} = \frac{V_L}{I_{L\min} - I_{L\max}}$$

$$I_{L\min} = I_E - I_{Z\max}$$

$$I_{L\min} = \frac{V_i - V_Z}{R} - 40$$

$$I_{L\min} = \frac{10}{22.2} - \frac{40}{1000}$$

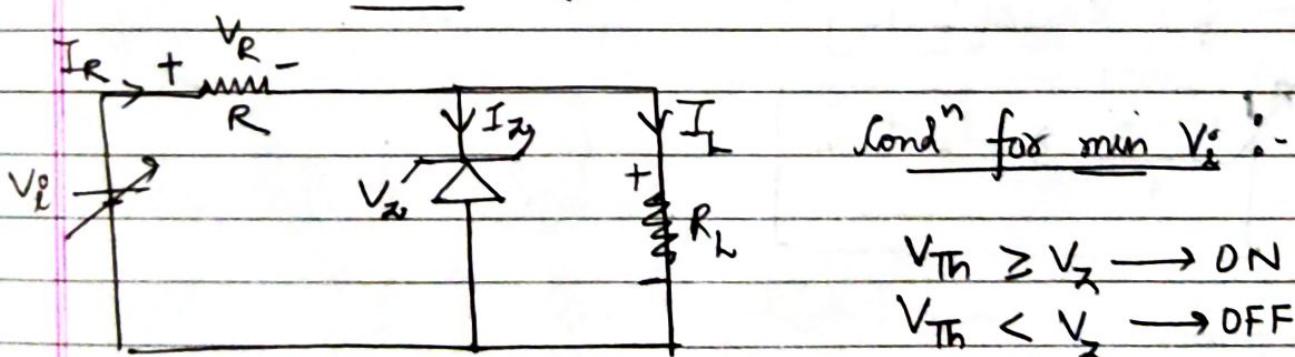
$$\Rightarrow 0.044 - 0.04$$

$$I_{L\min} = 45\text{mA} - 40\text{mA}$$

$$I_{L\min} = 5\text{mA}$$

$$R_{L\max} = \frac{10}{5} = 2\text{k}\Omega$$

### ③ Zener Diode as Voltage regulator [Variable $V_i$ & fixed $R_L$ ]



$$V_i - I_R \cdot R_L = 0$$

$$I = \frac{V_i}{R}$$

$$V_{Th} = V_z$$

$$R + R_L V_{Th} = V_L = I R_L$$

$$\frac{V_i R_L}{R + R_L} = V_z$$

$$V_{Th} = \frac{V_i R_L}{R + R_L}$$

$$V_{i\min} = \frac{V_z (R + R_L)}{R_L}$$

Cond<sup>n</sup> for  $V_{imax}$  :-

$V_{imax}$  is limited by  $I_{Z\max}$   $I_L = \frac{V_L}{R_L} = \frac{V_z}{R_L}$

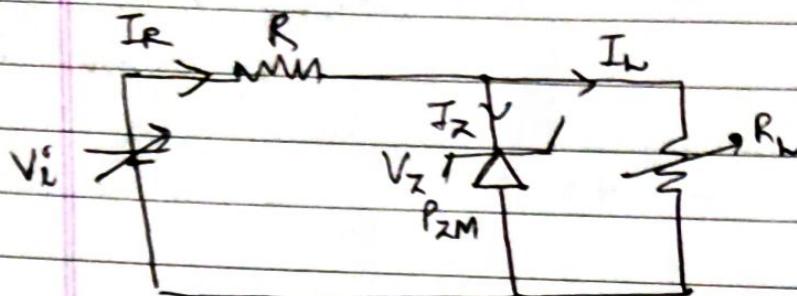
$$I_{R\max} = I_{Z\max} + I_{L\max}$$

$$V_{i\max} - V_{R\max} - V_z = 0$$

$$V_{i\max} = V_{R\max} + V_z$$

$$V_{i\max} = I_{R\max} R + V_z$$

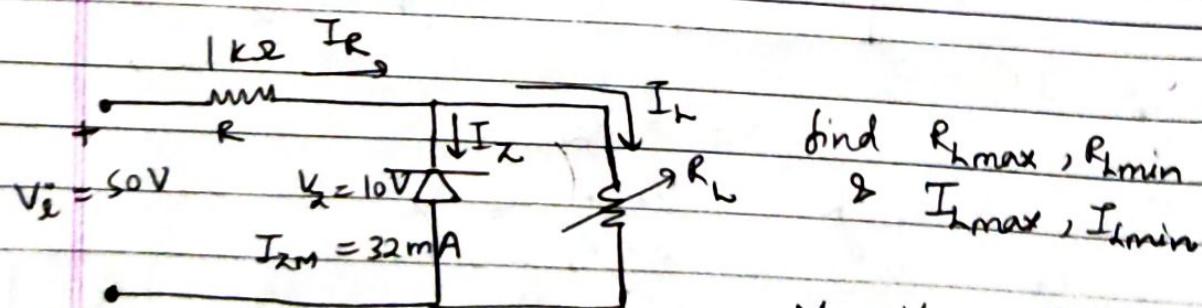
#### ④ Zener Diode as Voltage Regulator $[V_i \text{ & } R_L \text{ Variable}]$



$$\left. \begin{aligned} R_{\min} &= \frac{V_{i\max} - V_z}{I_{R\max}} \\ R_{\max} &= \frac{V_{i\min} - V_z}{I_{R\min}} \end{aligned} \right\}$$

Always True in Zener diode Problems

$$\frac{V_i - V_z}{R} \geq I_z + I_L$$



$$V_L = V_z = I_L \cdot R_L$$

$$I_D = \alpha \cdot R_{L\max}$$

Solve for  $R_{L\max}$ :  $\frac{10}{\alpha} = R_{L\max}$

$$R_{L\max} \rightarrow I_{L\min} \rightarrow I_{z\max}$$

$$I_R = I_L + I_{z\max}$$

$$I_R = \frac{V_i - V_z}{R}$$

$$I_R = \frac{40}{1}$$

$$(I_{z\max} = 32 \text{ mA})$$

Given

$$I_{L\min} = I_R - I_{z\max}$$

$$I_{L\min} = 40 - 32$$

$$I_{L\min} = 8 \text{ mA}$$

$$R_{L\max} = \frac{10}{8}$$

for  $R_{L\min}$ :

$$R_{L\min} \rightarrow I_{L\max} \rightarrow I_{Z\min}$$

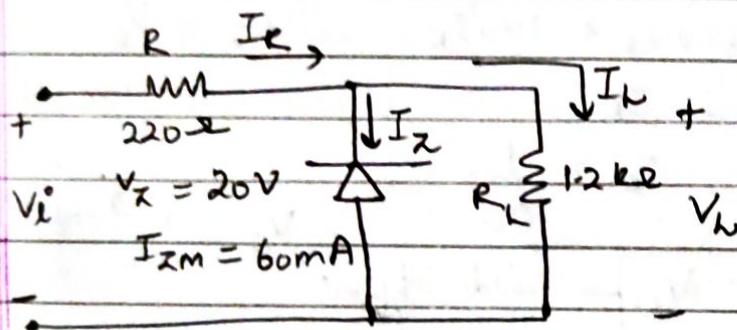
$$\begin{aligned} P_{\text{max}} &= \frac{V_Z}{2} I_{Zm} \\ &\Rightarrow 10 \cdot 32 \\ &= 320 \text{ mW} \end{aligned}$$

$$I_R = I_{Z\min} + I_{L\max}$$

$$\begin{aligned} I_{L\max} &= I_R - I_{Z\min} \\ I_{Z\min} &= I_R - \\ I_{L\max} &= 40 \end{aligned}$$

$$V_L = R_{L\min} \cdot 40$$

$$\frac{10k\Omega}{40} = \frac{P_{\text{min}}}{25} \quad R_{L\min} = \frac{10 \times 1000}{40} = 250 \Omega$$



find range of  $V_L$  that will maintain the zener diode in on state

for  $V_i$  to be min:

$$V_i - I_R R - I R_L = 0 \quad V_{Th} = V_Z$$

$$I = \frac{V_i}{R + R_L} \quad V_{Th} = V_L = I R_L$$

$$V_{Th} = \frac{V_i}{R + R_L} R_L$$

$$\frac{1.2 \times 10^3}{10}$$

$$V_{i\min} = \frac{20}{1200} (1200 + 220) = 23.67 \text{ V}$$

$$I_{R\max} = I_{Z\max} + I_L = 60 + 16.67$$

$$\begin{aligned} V_{i\max} &= I_{R\max} R + V_Z \\ &= 8(76.67)(0.22) + 20 \end{aligned}$$

$$\Rightarrow 36.87 \text{ V}$$

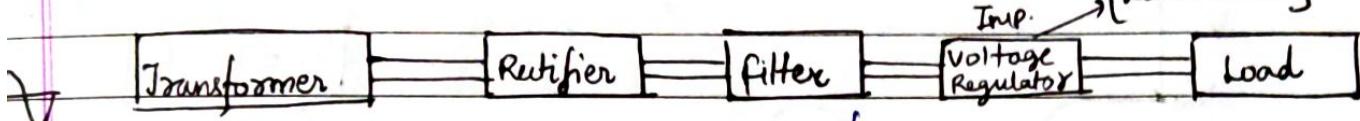
$$\begin{aligned} I_L &= \frac{V_L}{R_L} = \frac{20}{1.2} \\ &\Rightarrow 16.67 \end{aligned}$$

## Introduction to Diode Rectifier Circuits :-

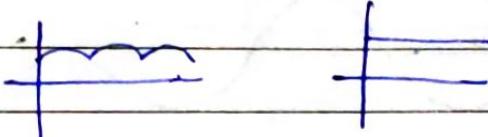
Rectification → Correction of error / mistakes.

- AC power is supplied in our house. [Because it is convenient to transmit]
- But most of appliances ~~use~~ used DC power, so rectifier is used as to convert A-C power to DC power.

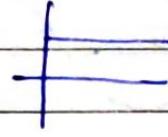
[Zener diode]



$$f = 50 \text{ Hz} \quad [\text{In India}]$$



$$f = 60 \text{ Hz} \quad [\text{In USA}]$$

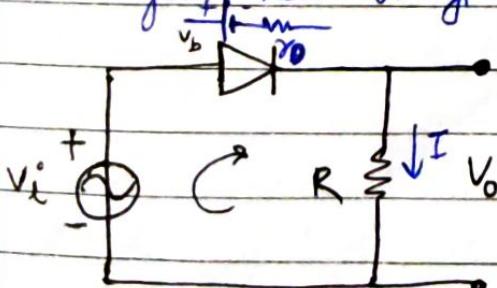


Types of Rectifier :- ① Half-wave Rectifier

- ② Full-Wave Rectifier :- a) Center Type  
b) Bridge Type

### HALF-WAVE RECTIFIER :-

- Only one half of the ac voltage is rectified, for the other half we get zero voltage.



Case of forward Biased : [Short circuit]

$$+V_i - V_b - I\gamma_D - IR = 0$$

$$I = \frac{V_i - V_b}{R + \gamma_D}$$

$$\gamma_D \ll R$$

$$V_0 = IR$$

$$V_0 = \left( \frac{V_i - V_b}{R + \gamma_D} \right) R$$

$$V_0 = \left( \frac{R}{R + \gamma_D} \right) V_i$$

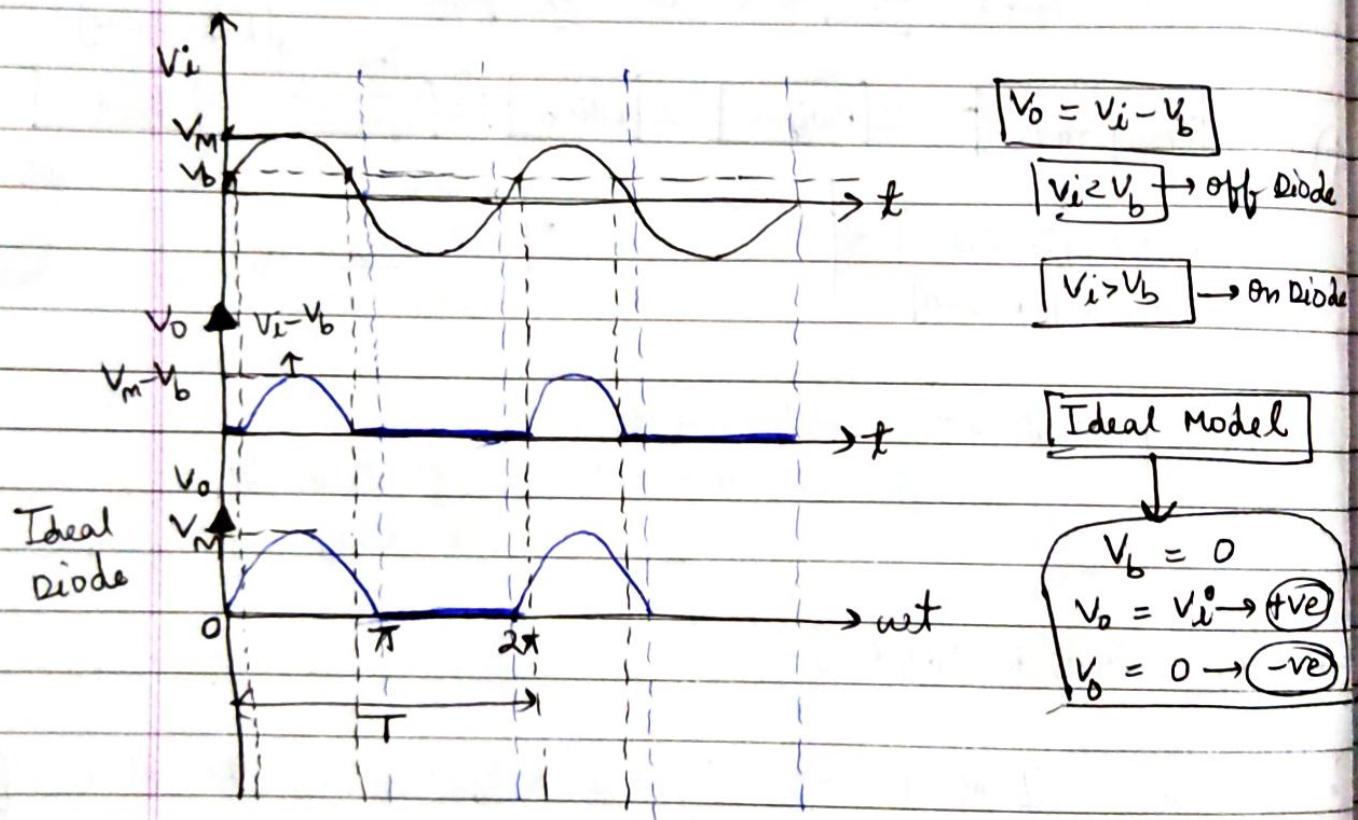
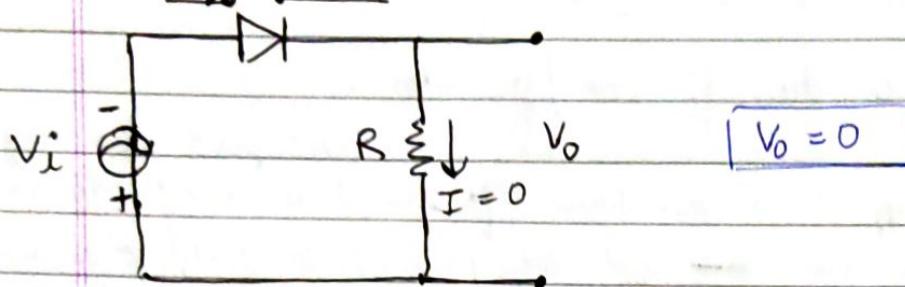
$$- \left( \frac{R}{R + \gamma_D} \right) V_b$$

$$V_0 = V_i - V_b$$

$$V_b = 0.7 \text{ V} \rightarrow \text{Silicon}$$

$$V_b = 0.3 \text{ V} \rightarrow \text{Germanium}$$

Case of Reverse Biased : [open circuit]



Average output voltage :-

$$V_0 = V_m \sin \omega t \quad [\alpha \leq \omega t < \pi]$$

$$V_0 = 0 \quad \pi \leq \omega t \leq 2\pi$$

$$V_{avg} = \frac{1}{2\pi} \int_0^{2\pi} V_0 d(\omega t)$$

$$\Rightarrow \frac{1}{2\pi} \left[ \int_0^{\pi} V_m \sin \omega t d(\omega t) + \int_{2\pi}^0 0 d(\omega t) \right]$$

On solving

$$V_{avg} = \frac{V_m}{\pi} = 0.318 V_m$$

Avg load current :-

$$I_{avg} = \frac{V_{avg}}{R} \Rightarrow \frac{V_m / \pi}{R} \Rightarrow \frac{I_M}{\pi}$$

Half Wave Rectifier [RMS Load current & RMS Load voltage]

RMS Load current :-

$$\sqrt{\text{mean}[S^2 \cdot (I)]}$$

$$I_{rms} = \sqrt{\frac{\int_0^{2\pi} I^2 d(wt)}{2\pi - 0}}$$

$$I = I_M \sin wt \quad 0 \leq wt \leq \pi$$

$$I = 0 \quad \pi \leq wt \leq 2\pi$$

$$\Rightarrow \left[ \frac{1}{2\pi} \int_0^{2\pi} I_M^2 \sin^2 wt d(wt) + \int_0^\pi 0 d(wt) \right]^{1/2}$$

$$\Rightarrow \left[ \frac{I_M^2}{2\pi} \int_0^\pi \sin^2 wt d(wt) \right]^{1/2}$$

$$\cos 2\theta = 1 - 2\sin^2 \theta$$

$$\sin^2 \theta = \frac{1}{2}(1 - \cos 2\theta)$$

$$\Rightarrow \frac{I_M^2}{2\pi} \left[ \frac{1}{2} [1 - \cos 2wt] d(wt) \right]^{1/2}$$

$$\Rightarrow \left[ \frac{I_M^2}{4\pi} \left[ wt - \frac{\sin 2wt}{2} \right]_0^\pi \right]^{1/2}$$

$$\Rightarrow \left[ \frac{I_M^2 \times \pi}{4\pi} \right]^{1/2} \Rightarrow \frac{I_M}{2} \Rightarrow I_{rms}$$

$$V_{rms} = I_{rms} R$$

$$= \frac{V_m}{2R} \cdot R$$

$$V_{rms} = \frac{V_m}{2}$$

## HALF WAVE RECTIFIER [FORM FACTOR]

form factor :- It is defined as the ratio of rms load voltage and average load voltage.

$$\text{Form factor} = \frac{V_{\text{rms}}}{V_{\text{avg}}}$$

rms value:

$$5V_{\text{rms}} = 5V_{\text{dc}}$$

rms value ≤ peak value

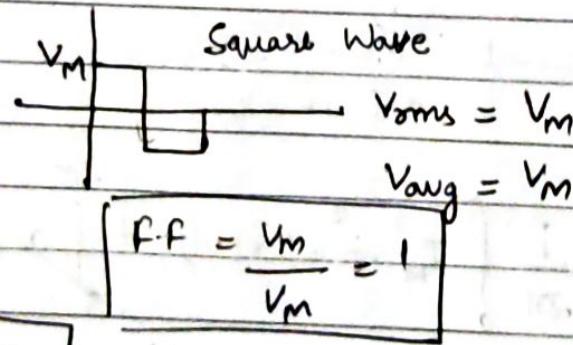
$$f.f. \geq 1$$

$$|\text{rms} \geq \text{avg}|$$

$$V_{\text{rms}} = \frac{V_m}{2}$$

$$V_{\text{avg}} = \frac{V_m}{\pi}$$

$$f.f. = \frac{V_m/2}{V_m/\pi} \Rightarrow \frac{\pi}{2} = \frac{3.14}{2} = 1.57 > 1$$



$$V_{\text{rms}} = 1.57 V_{\text{avg}}$$

## HALF WAVE RECTIFIER [RIPPLE FACTOR]

Ripple factor :- The output current contains both ac and dc components. The ripple factor measures the percentage of ac component in the rectified output.

The ideal value of Ripple factor should be zero.  
 $\gamma = 0\%$       a.c comp = 0 =  $\gamma = 0$

$$\gamma = \frac{\text{rms value of ac comp. of output}}{\text{avg. value of output}}$$

$$I = I_{ac} + I_{dc} \Rightarrow I_{ac} = I - I_{dc}$$

$$I_{ac\text{ rms}} = \sqrt{\frac{1}{2\pi} \int_0^{2\pi} I_{ac}^2 d(\omega t)}$$

$$\text{Ripple factor} = \sqrt{(F.F)^2 - 1}$$

$$F.F = \frac{I_{\text{rms}}}{I_{dc}}$$

$$\eta \% = \sqrt{(F.F)^2 - 1} \times 100\%$$

## HALF WAVE RECTIFIER [P.I.V and Efficiency]

Efficiency :- It is defined as ratio of dc power available at the load to the input ac power.

$$\eta \% = \frac{P_{\text{load}}}{P_{\text{in}}} \times 100\%$$

$$P = VI$$

$$P = I^2 R$$

$$\Rightarrow \frac{I_{dc}^2 R}{I_{\text{rms}}^2} \times 100\%$$

$$I_{dc} = \frac{I_m}{\pi}, \quad I_{\text{rms}} = \frac{I_m}{2}$$

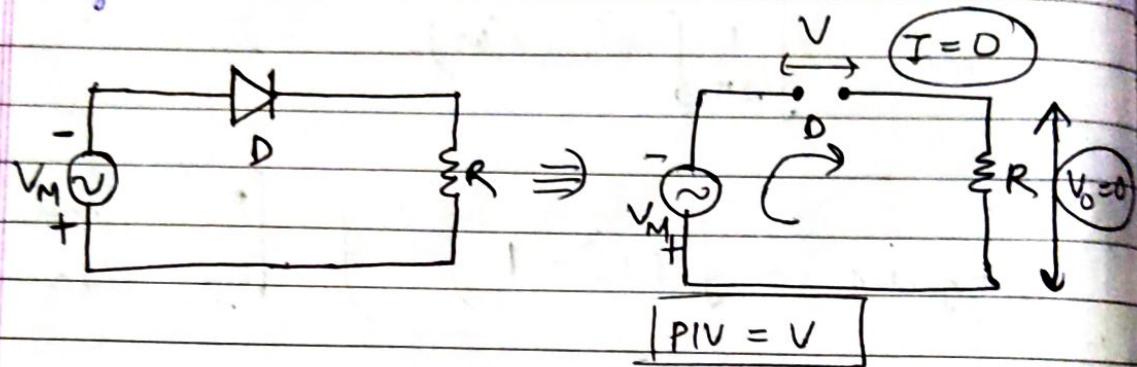
$$\Rightarrow \frac{\frac{I_m^2}{\pi^2} R}{\frac{I_m^2}{4}} \times 100\% \Rightarrow \frac{4}{\pi^2} \times 100\%$$

$$\eta \% = 40.56\% \rightarrow \text{Low efficiency}$$

disadvantage of Half wave Rectifier.

## Peak Inverse Voltage [PIV]:

Max. reverse bias voltage that can be applied across the diode before entering to the zener or breakdown region.



$$-V_M + V = 0$$

$$V = V_M$$

$$\boxed{\text{PIV} \geq V_M}$$

$$\boxed{\text{PIV} = V_M}$$

## \* Full wave Bridge Rectifier :-

100 %

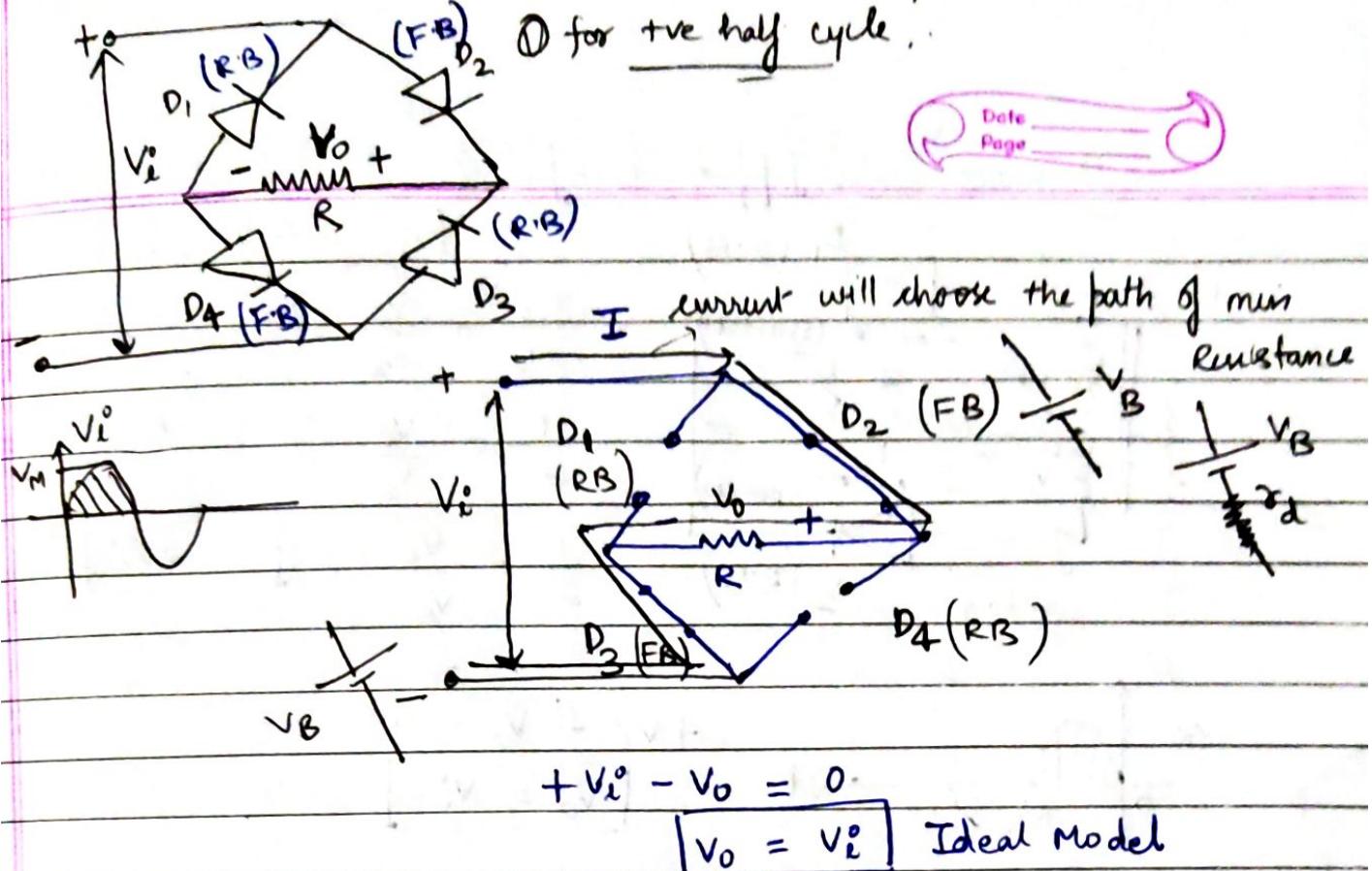
Disadvantages of

H.W.R :- i) ~~(+ve)~~ half cycle  $\rightarrow V_o = V_i = V_m \sin \omega t$   
~~(-ve)~~ half cycle  $\rightarrow V_o = 0$

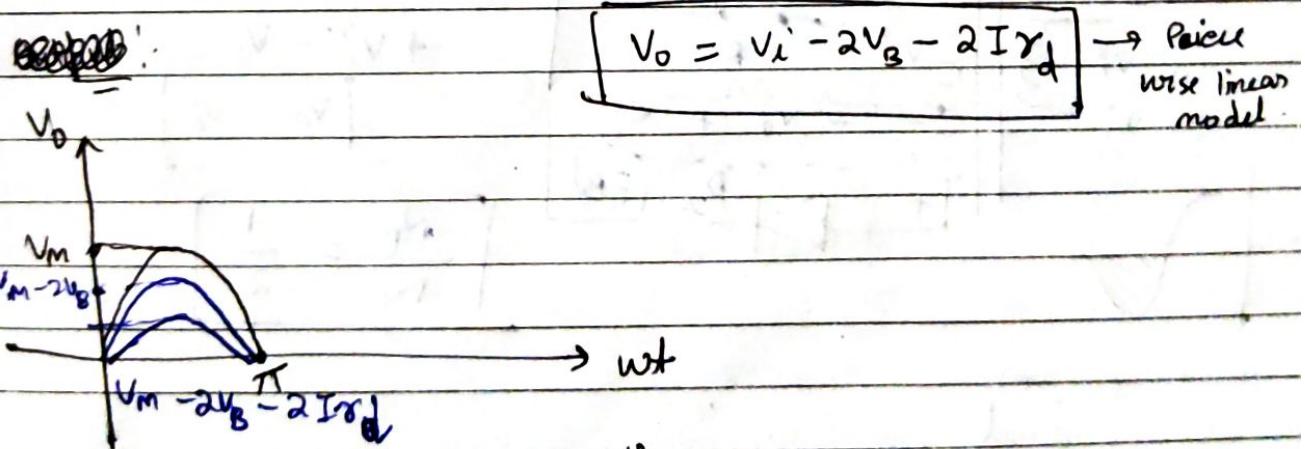
ii) Ripple factor (%) = 121 %

iii)  $\eta \% = 40.56 \% \rightarrow$  low efficiency

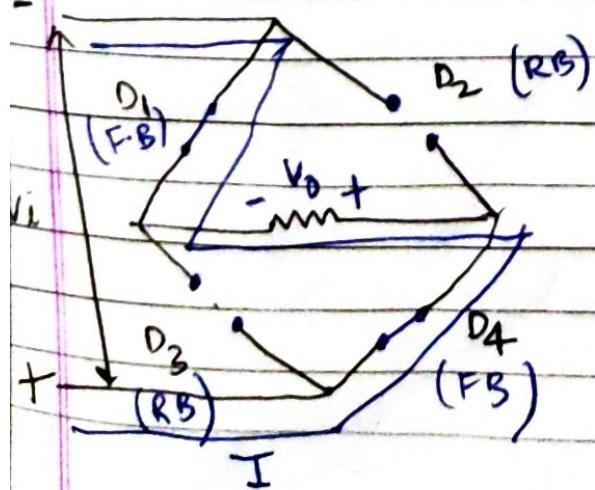
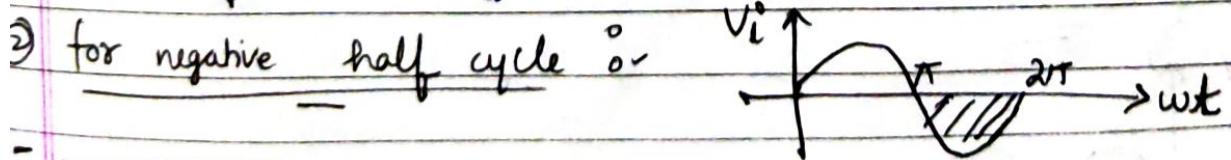
- That's why we use full wave rectifier.



$| V_o = V_i^o - 2V_B |$  constant voltage drop model



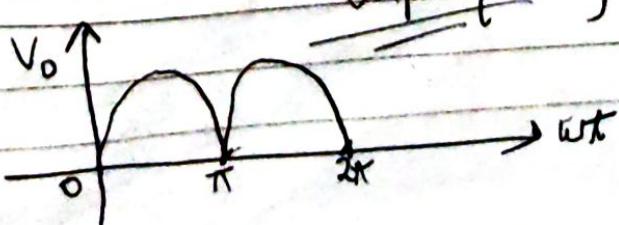
2) for negative half cycle :-



$+V_i^o - V_o = 0$

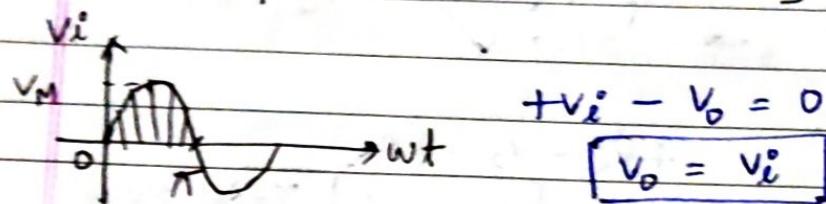
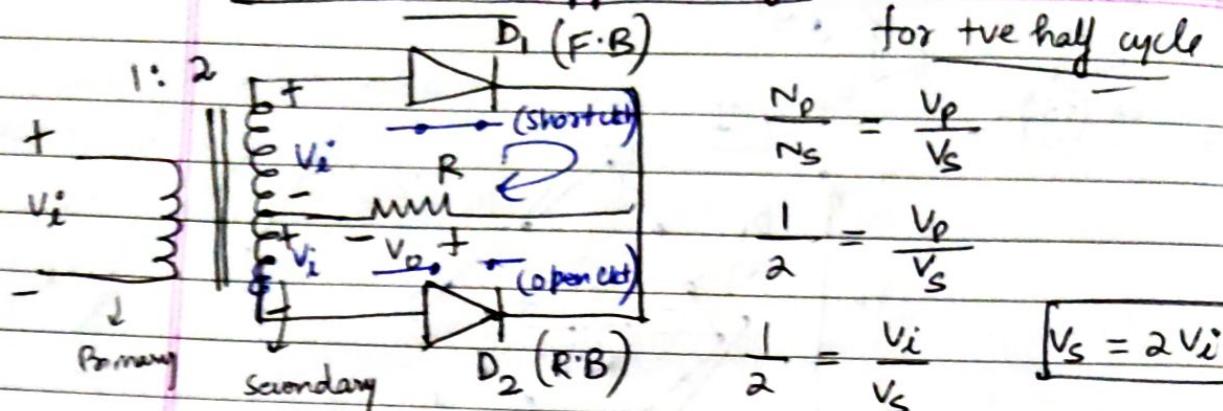
$| V_o = V_i^o |$

output [final]

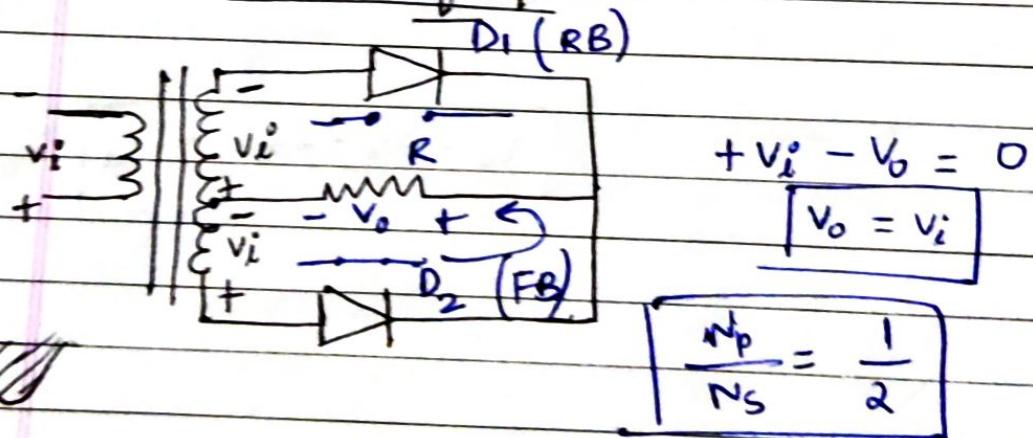


## Full wave Center Tapped Rectifier :

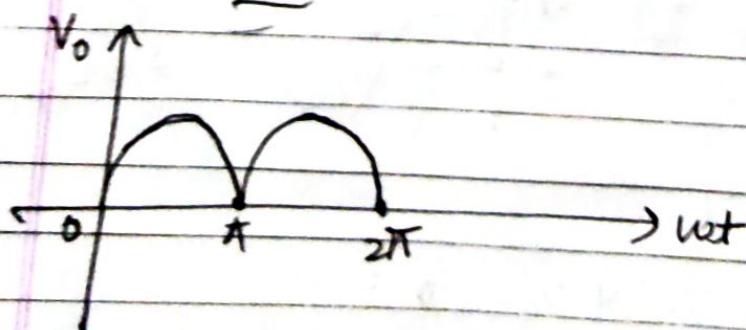
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for negative half cycle :-



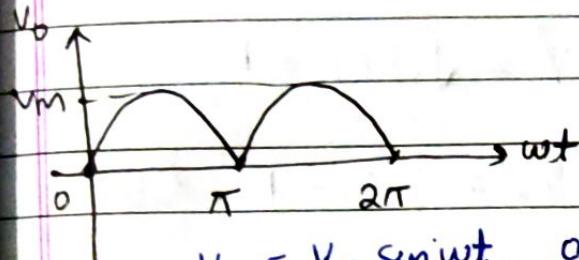
final waveform :-



# Full wave Rectifier [Avg. Load current & Avg load voltage]

load

\* Avg (dc) voltage :-



$$V_o = V_m \sin \omega t \quad 0 \leq \omega t \leq \pi$$

$$\begin{aligned} V_{avg} &= V_{dc} = \frac{1}{\pi} \int_0^{\pi} V_m \sin \omega t \, d(\omega t) \\ &= \frac{V_m}{\pi} \left[ -\cos \omega t \right]_0^{\pi} \end{aligned}$$

$$= \frac{V_m}{\pi} \left[ -\cos \pi - (-\cos 0) \right]$$

$$\boxed{V_{avg} = \frac{2V_m}{\pi}}$$

$$V_{avg} = \frac{V_m}{\pi} [1+1] \Rightarrow \frac{2V_m}{\pi}$$

Avg(d)load current :-

$$I_{avg} = \frac{V_{avg}}{R} = \frac{2V_m}{\pi R} \Rightarrow \boxed{\frac{2I_m}{\pi}}$$

$$\cos 2\theta = 1 - 2 \sin^2 \theta$$

RMS Load current & RMS Load Voltage :-

RMS Load current :-

$I \Rightarrow$  Load current

$$I = I_m \sin \omega t \quad 0 \leq \omega t \leq \pi$$

$$I_{rms} = \left[ \frac{I_m^2}{\pi} \int_0^{\pi} \sin^2 \omega t \, d(\omega t) \right]^{1/2}$$

$$I_{rms} = \frac{I_m^2}{\pi} \int_0^{\pi} \frac{1}{2} (1 - \cos 2\omega t) \, d(\omega t)$$

$$I_{rms} = \left[ \frac{1}{\pi} \int_0^{\pi} I^2 \, d(\omega t) \right]^{1/2}$$

$$I_{rms} = \left[ \frac{1}{\pi} \int_0^{\pi} I_m^2 \sin^2 \omega t \, d(\omega t) \right]^{1/2}$$

on solving

$$\boxed{I_{rms} = \frac{I_m}{\sqrt{2}}}$$

$$V_{rms} = I_{rms} R \\ = \frac{I_m R}{\sqrt{2}}$$

$$\boxed{V_{rms} = \frac{V_m}{\sqrt{2}}}$$

$$= \frac{V_m}{\sqrt{2}}$$

# Full wave Rectifier [Form factor & Ripple factor]

Date \_\_\_\_\_  
Page \_\_\_\_\_

Form factor:

$$F.F = \frac{V_{rms}}{V_{avg}} \text{ or } \frac{I_{rms}}{I_{avg}}$$

$$F.F = \frac{V_m / \sqrt{2}}{2V_m / \pi}$$

$$F.F = \frac{\pi}{2\sqrt{2}}$$

$F.F = 1.11$

Ripple factor:

$$\sqrt{\%} = \sqrt{(F.F)^2 - 1}$$

$$\sqrt{\%} = \sqrt{(1.11)^2 - 1} \times 100$$

$$\sqrt{\%} = \sqrt{(1.11)^2 - 1} \times 100$$

$$\boxed{\sqrt{\%} = 48\% \text{ ac component}}$$

In H.W.R.

$$\boxed{\sqrt{\%} = 121\%}$$

\* So  $\sqrt{\%}$  is reduced by 73% by using F.W.R.

Efficiency & PIV %:-

Efficiency:

$$\eta \% = \frac{\text{Output dc power}}{\text{input ac power}} \times 100\%$$

$$P = I^2 R$$

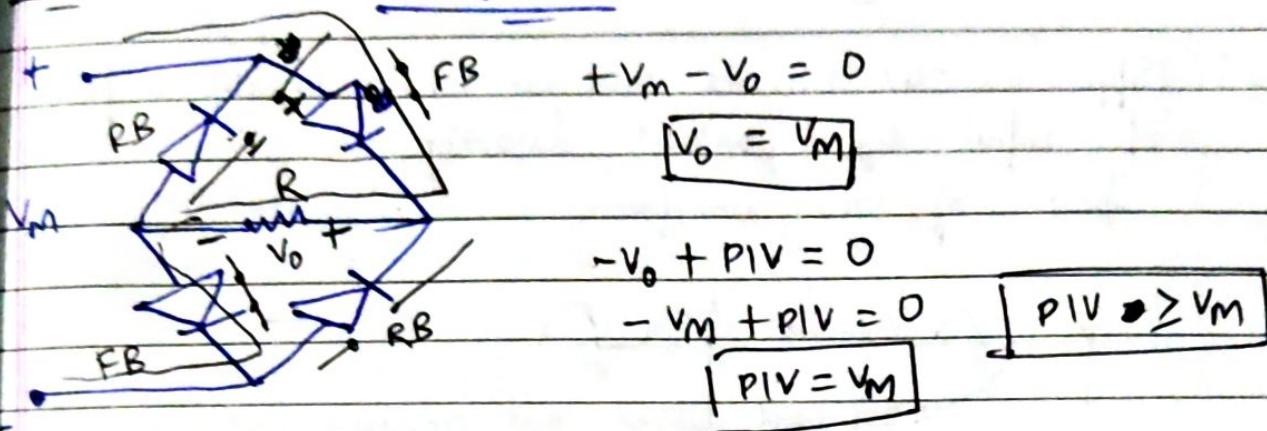
$$I_{dc} = \frac{2I_m}{\pi}$$

$$= \frac{I_{dc}^2 R}{I_{rms}^2 R} \times 100\% \quad *$$

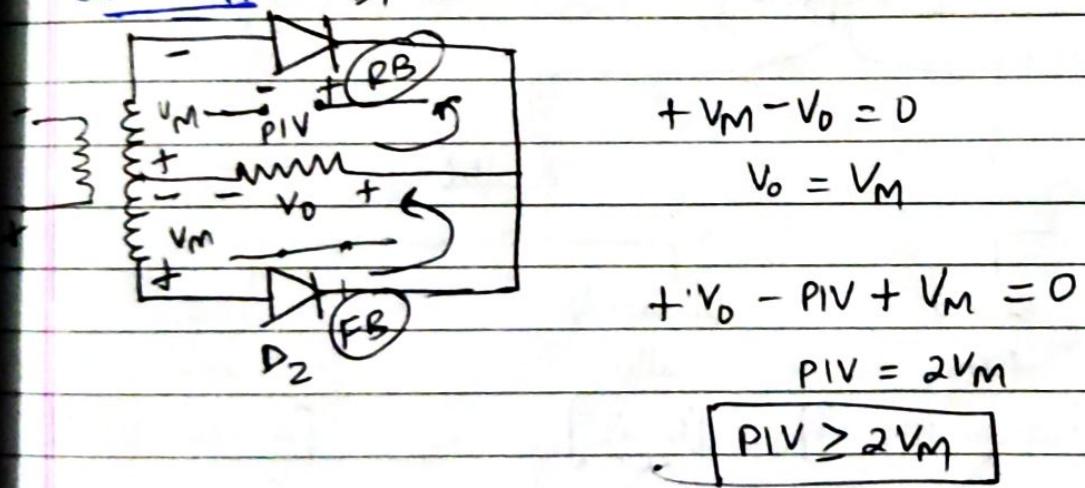
$$I_{rms} = \frac{I_m}{\sqrt{2}}$$

$$\Rightarrow \frac{4I_m^2}{\pi^2 I_m^2} \cdot 2 \times 100\% \quad \boxed{\eta \% = 81.13\%}$$

PIV: full wave Bridge Rectifier:

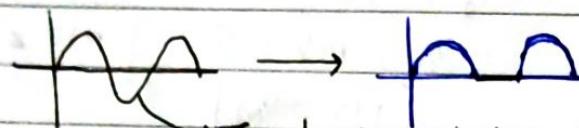


Center Tapped Rectifier  $D_1 =$



## Introduction to Clippers :-

Clippers :- Clippers are the networks that use diodes to clip a portion of input signal without distorting the remaining part of the waveform.



This part clipped and remaining part is same.

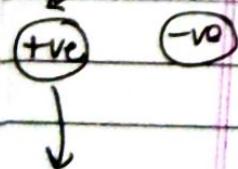
→ Clippers are also used to eliminate the noise effect in ~~noise~~ signal.

Series

Parallel

Unbiased  
series

[Basic]



Biased  
series

[Additional DC source]



Unbiased  
parallel

[Basic]



Biased  
parallel

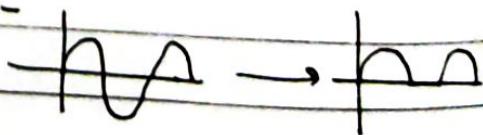
[Additional DC source]



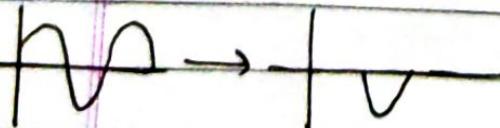
Positive portion of waveform  
is clipped.

→ -ve portion of waveform  
is clipped.

Ex :-



Ex :-

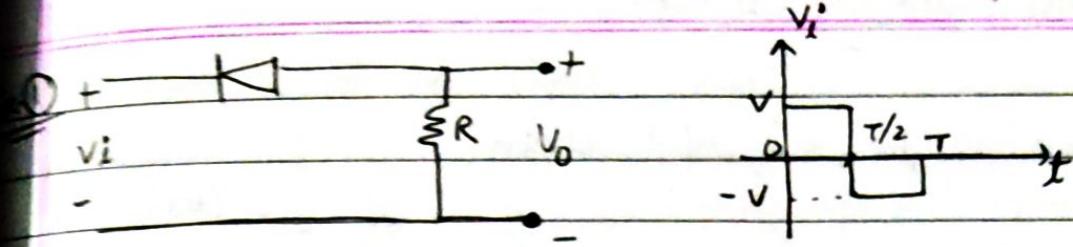


→ Series Clipper → Diode is connected in series with Resistor

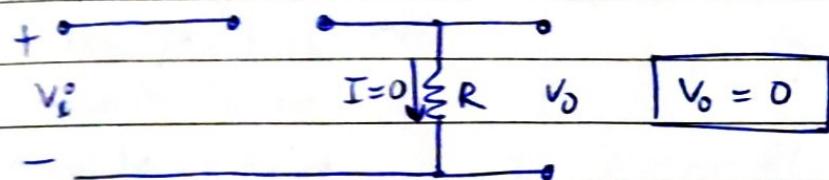
→ Parallel clipper → " " " " " parallel " "

→ Biased clipper → Additional DC source applied.

→ Unbiased clipper → No Add' DC source " .

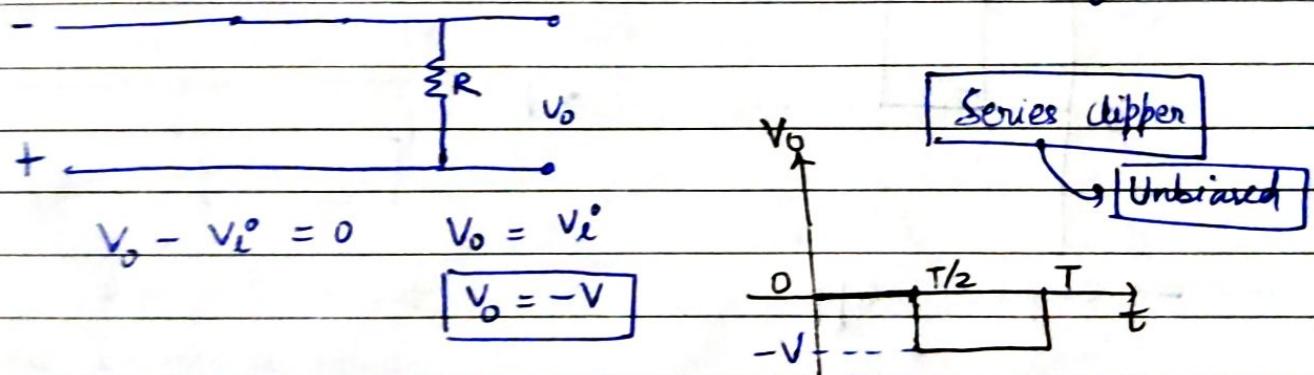


for the half cycle  $[0 \rightarrow T/2]$   
diode is Reverse Biased [open circuit]  $\rightarrow [i = 0]$



for -ve half cycle  $[T/2 \rightarrow T]$

diode is forward Biased [short circuit]



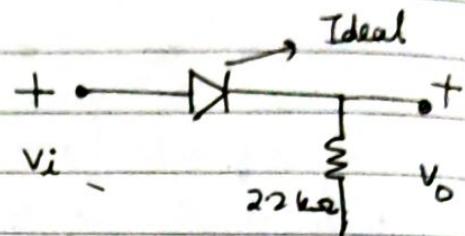
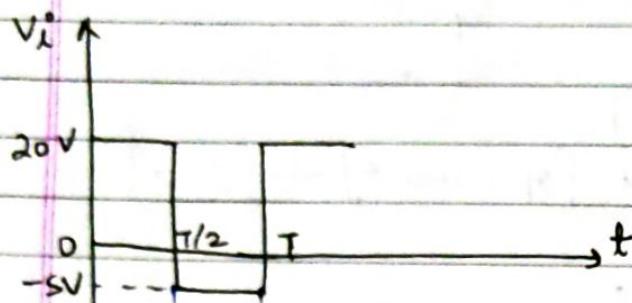
As we can see in output positive portion is clipped out, so it is positive clipper.

finally this circuit is Positive Unbiased Series clipper.

## UNBIASED SERIES CLIPPERS

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Page \_\_\_\_\_

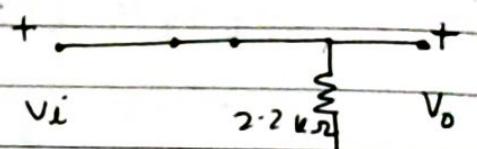
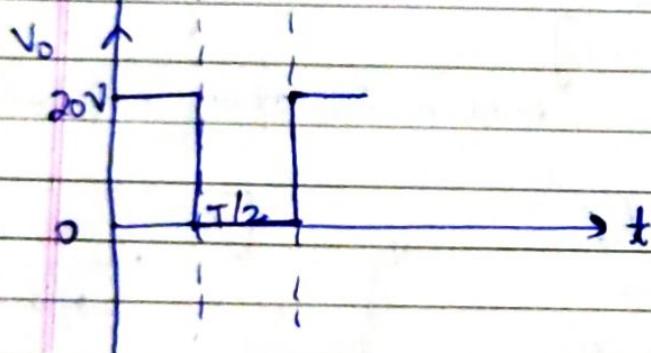
Q. Determine  $V_o$  for the input shown.



for first half cycle ( $0 \rightarrow T/2$ )

diode is forward

Biased (short circuit)



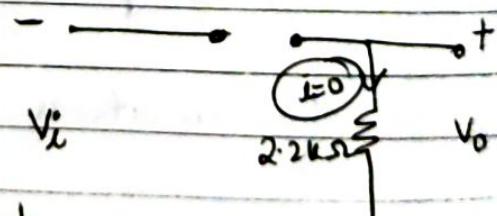
$$V_o = V_i$$

→ Negative clipper

for next half cycle ( $T/2 \rightarrow T$ )

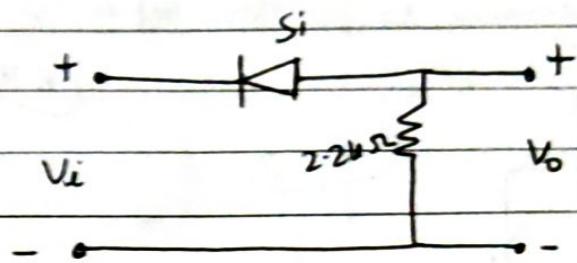
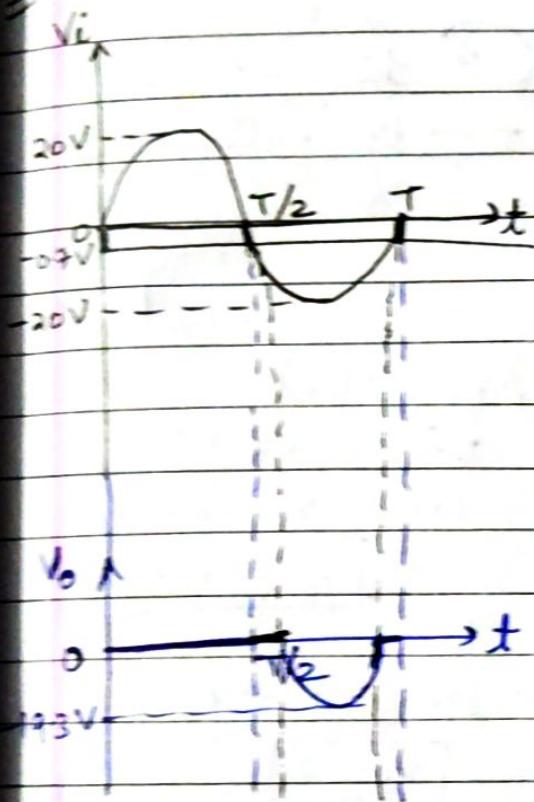
diode is Reverse Biased

(open circuit)

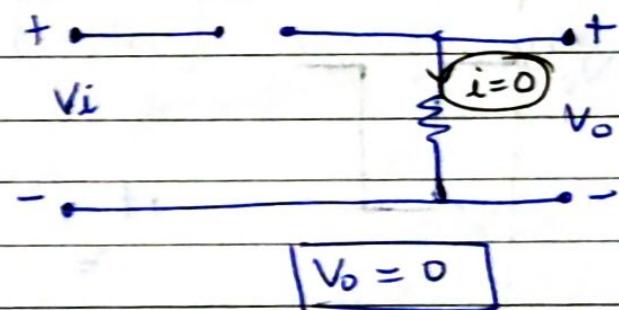


$$V_o = 0$$

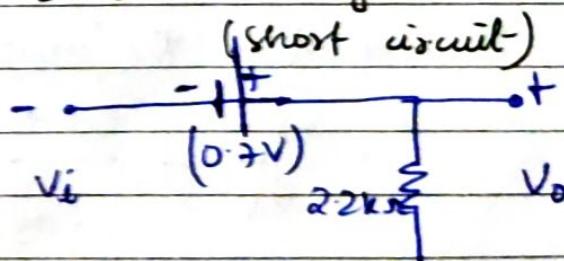
Determine  $V_o$  for the input shown:



for first half cycle ( $0 \rightarrow T/2$ )  
Si diode is reversed biased  
(open circuit)



for next half cycle ( $T/2 \rightarrow T$ )  
Si diode is forward Biased



Here we can see in output waveform that the portion is clipped so it is tve clipper.

$$-V_i + 0.7 - V_o = 0$$

$$V_o = 0.7 - V_i$$

$$V_o = 0.7 - (20)$$

$$V_o = -19.3\text{ V}$$

e.g. valid when

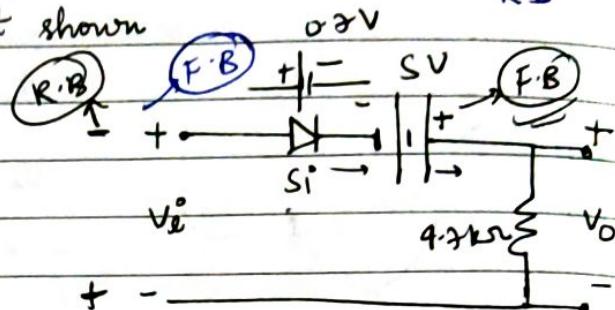
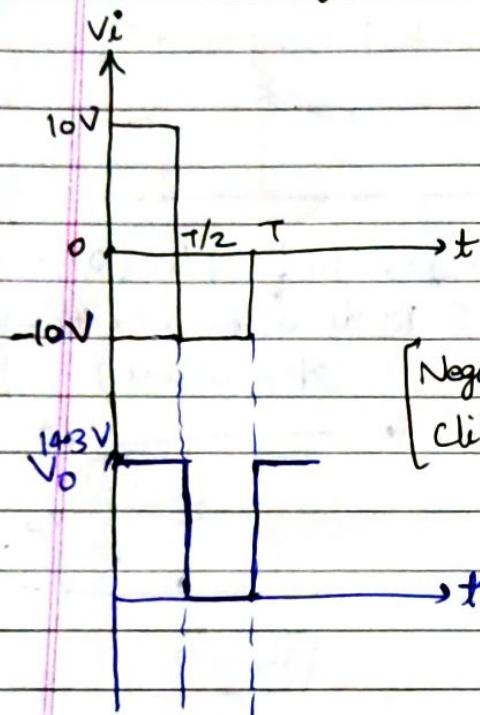
$$V_i > V_b$$

$$(0.7\text{ V})$$

Only considered that DC source & forgot  $V_i$   
 & find the state of diode

## BIASED SERIES CLIPPERS: (Add "DC Source")

① Determine  $V_o$  for the input shown



for  $(0 \rightarrow T/2)$

$$V_i^o - 0.7V + 5V = V_o \\ 10 - 0.7V + 5V = V_o$$

$$\boxed{V_o = 14.3V}$$

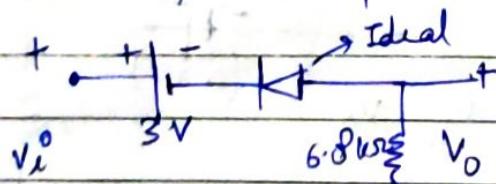
for  $(T/2 \rightarrow T)$

$$\boxed{V_o = 0}$$

'5V is not enough  
sufficient to make diode

② Determine  $V_o$  for the input shown (F.B.) because it is

less than  $V_i \geq 10V$



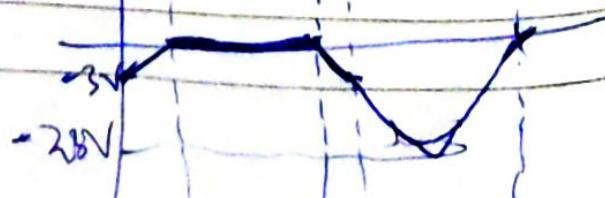
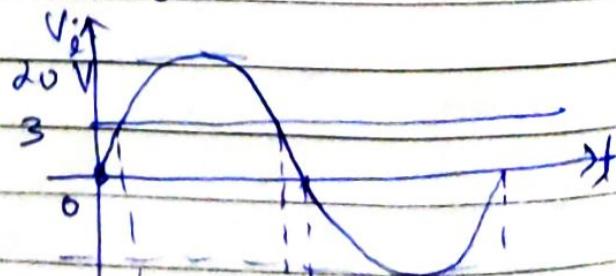
$$V_i^o = 0 \quad V_o = -3V$$

$$\text{so for } (0 \rightarrow T/2) \quad F.B. \rightarrow V_i^o < 3V \rightarrow V_o = V_i^o - 3V$$

$$\Leftrightarrow R.B. \rightarrow V_i^o > 3V \rightarrow V_o = 0$$

$$\text{for } (T/2 \rightarrow T) \quad \boxed{V_o = -V_i^o - 3V}$$

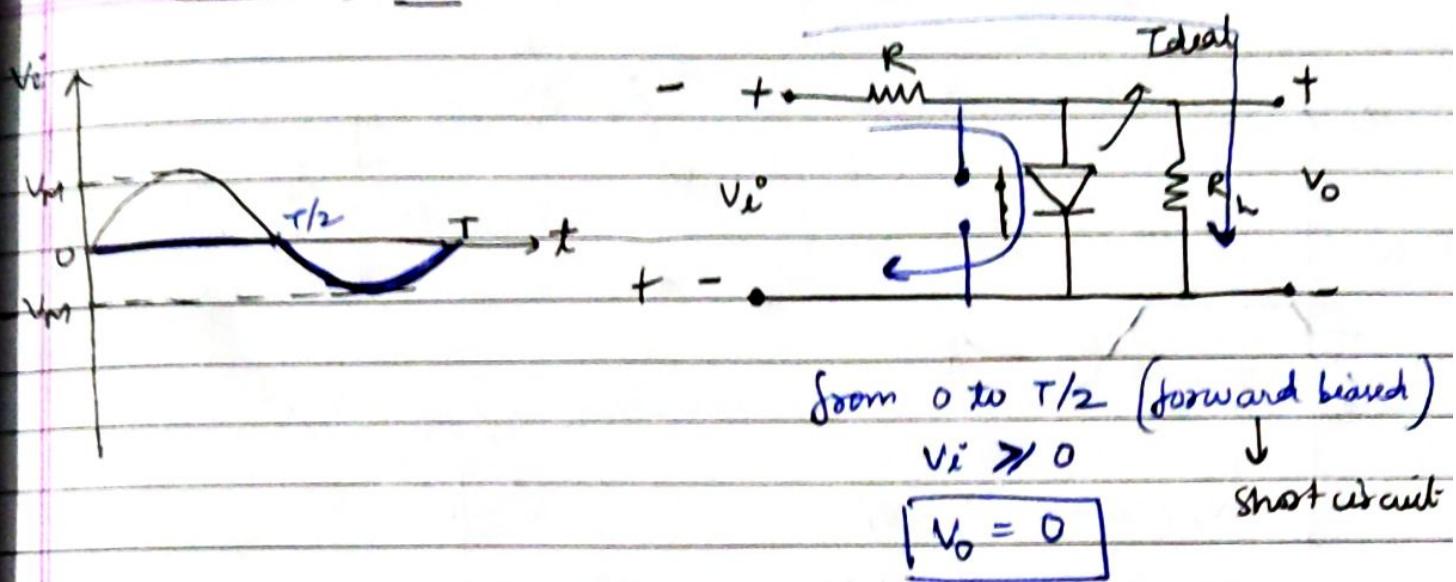
$$V_o = -20 - 3 \\ = -23V$$



(Diode is connected parallel with load resistance)

### UNBIASED PARALLEL CLIPPERS

Date \_\_\_\_\_  
Page \_\_\_\_\_



from  $T/2$  to  $T$

$$+V_i + V_o + V_d = 0$$

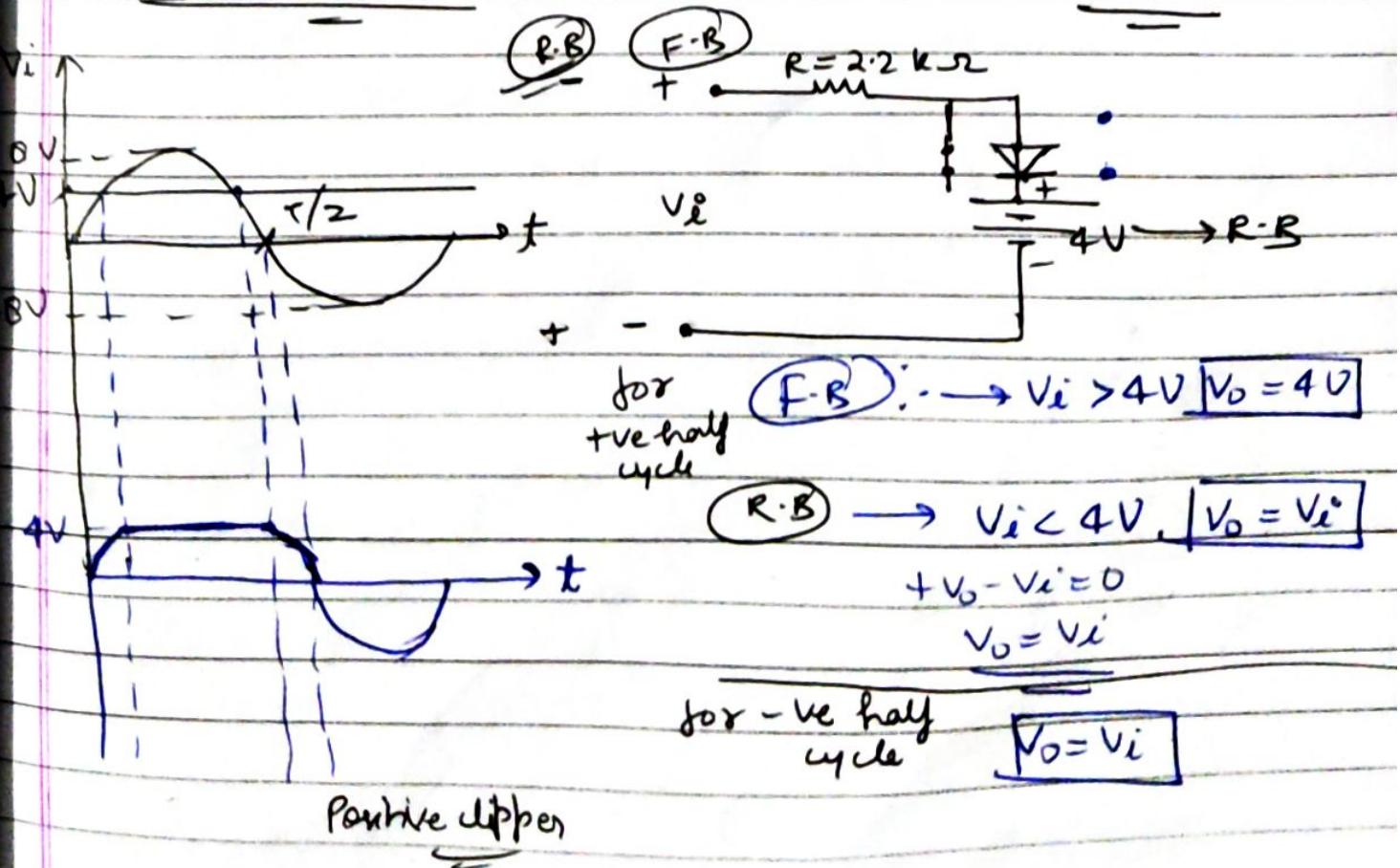
$$V_o = V_R - V_i^0$$

$$\boxed{V_o = -V_i}$$

Resistance is very small

### BIASED PARALLEL CLIPPERS

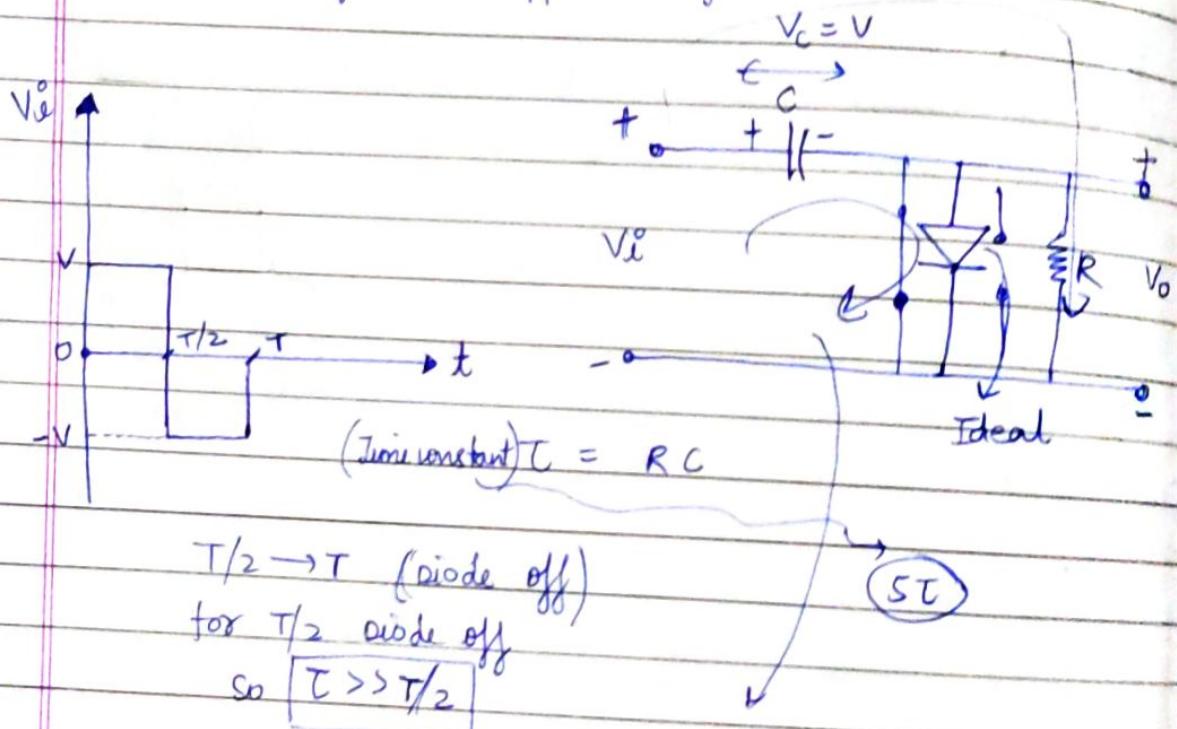
$$V_o \quad V_R = 0$$



Clampers :-

\* Assume discharging time of capacitor is very large ( $\tau \gg ST$ )  
 so capacitor give const voltage  $= V$

A clumper is a network constructed of a diode, a resistor, and a capacitor that shifts the waveform to a different dc level without changing the appearance of the applied signal.



for  $(0 \rightarrow T/2)$

[Diode on] → FB → short ckt

$$V_i^o = +V$$

$$\boxed{V_o = 0}$$

In this loop  $R=0$

$$\text{so } \boxed{\tau = 0}$$

$$+V_i^o - V_C = 0$$

$$V_C = V_i^o$$

$$\boxed{V_C = +V}$$

for  $(T/2 \rightarrow T)$

$$V_C = V$$

Diode is R-B (open ckt)

$$+V_o^o + V_o + V = 0$$

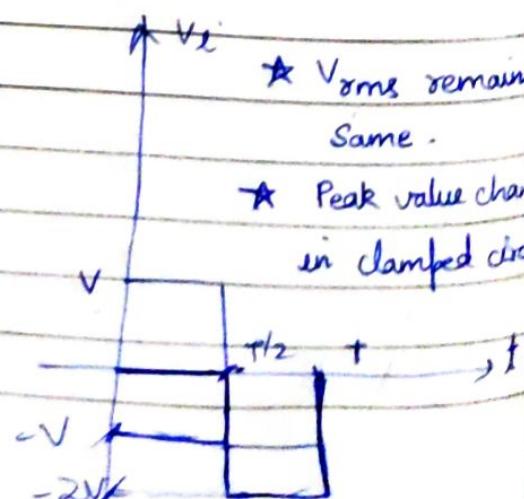
$$V_o = -V - V_i^o$$

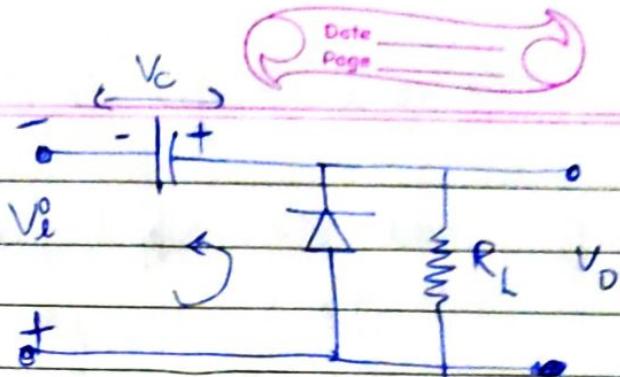
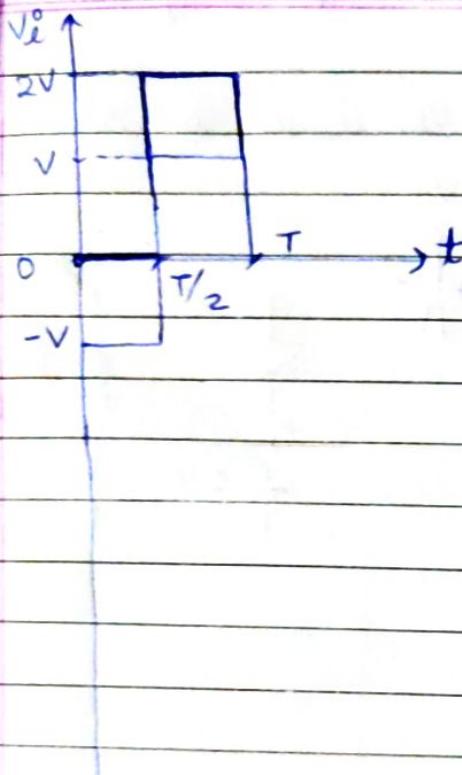
$$V_o = -2V$$

\*  $\boxed{\tau \gg T/2}$

\*  $V_{rms}$  remains same.

\* Peak value changes in clamped circuit





0 to  $T/2$  (Diode is F-B)

$$V_i^o = -V$$

$$\boxed{V_o = 0}$$

$$-V_o = -V$$

$$V_i^o = V$$

$$+V_i^o - V_c = 0$$

$$V_c = V_i^o$$

$$V_c = -(-V_i) \quad \bullet$$

$T/2 \rightarrow T$  :-

$$V_o = V_i^o + V_c$$

$$= V + V$$

$$\boxed{V_o = 2V}$$